CLAIMS

1. Process for fabricating a substrate for a radiofrequency filter by joining a piezoelectric layer to a carrier substrate via an electrically insulating layer, characterized in that it comprises the steps of depositing the electrically insulating layer by spin coating an oxide belonging to the family of SOGs (spin-on glasses) on the surface of the piezoelectric layer to be joined to the carrier substrate, followed by an anneal for densifying said electrically insulating layer before joining.

2. Process according to the preceding claim, wherein the thickness of the piezoelectric layer is greater than 5 µm, preferably greater than 10 µm.

3. Process according to one of the preceding claims, wherein the surface of the piezoelectric layer to be joined to the carrier substrate has a rough surface suitable for reflecting a radiofrequency wave.

4. Process according to the preceding claim, wherein the rough surface of the piezoelectric layer has a roughness of greater than 1 µm, preferably greater than 3 µm.

5. Process according to one of the preceding claims, wherein the carrier substrate is made of silicon material.

6. Process according to one of the preceding claims, wherein the carrier substrate made of silicon material comprises a trapping layer towards the interface to be joined with the piezoelectric layer.

7. Process according to one of the preceding claims, wherein the piezoelectric layer is made of lithium niobate or lithium tantalate.